

ABSTRACT OF THE DISCLOSURE

A semiconductor device comprises a semiconductor substrate, and a non-volatile memory cell provided on the semiconductor substrate, the non-volatile memory
5 cell comprising a tunnel insulating film having a film thickness periodically and continuously changing in a channel width direction of the non-volatile memory cell, a floating gate electrode provided on the tunnel insulating film, a control gate electrode
10 provided above the floating gate electrode, and an interelectrode insulating film provided between the control gate electrode and the floating gate electrode.